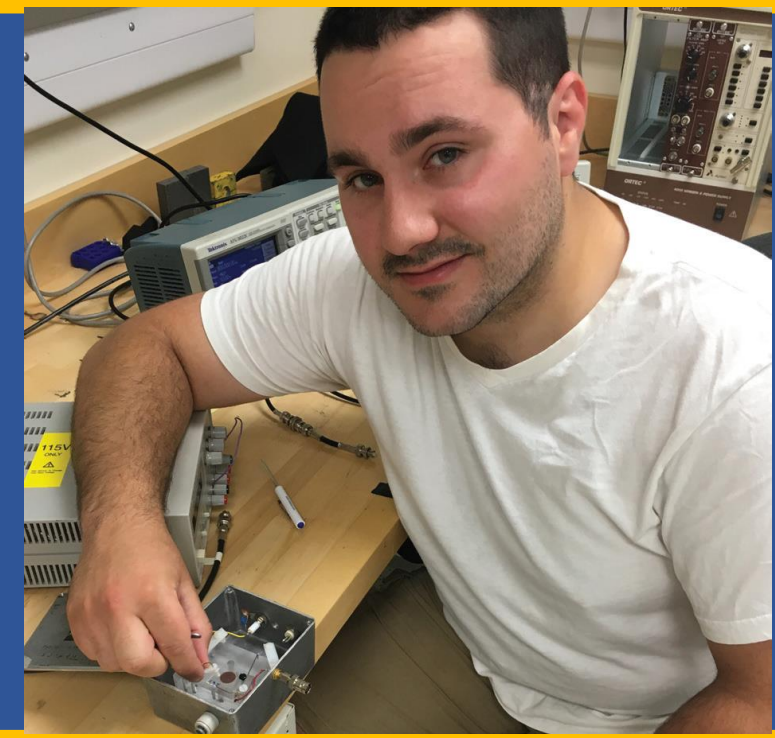


# Engineering of a High Sensitivity X-Ray Detector for Low-Dose Medical Imaging

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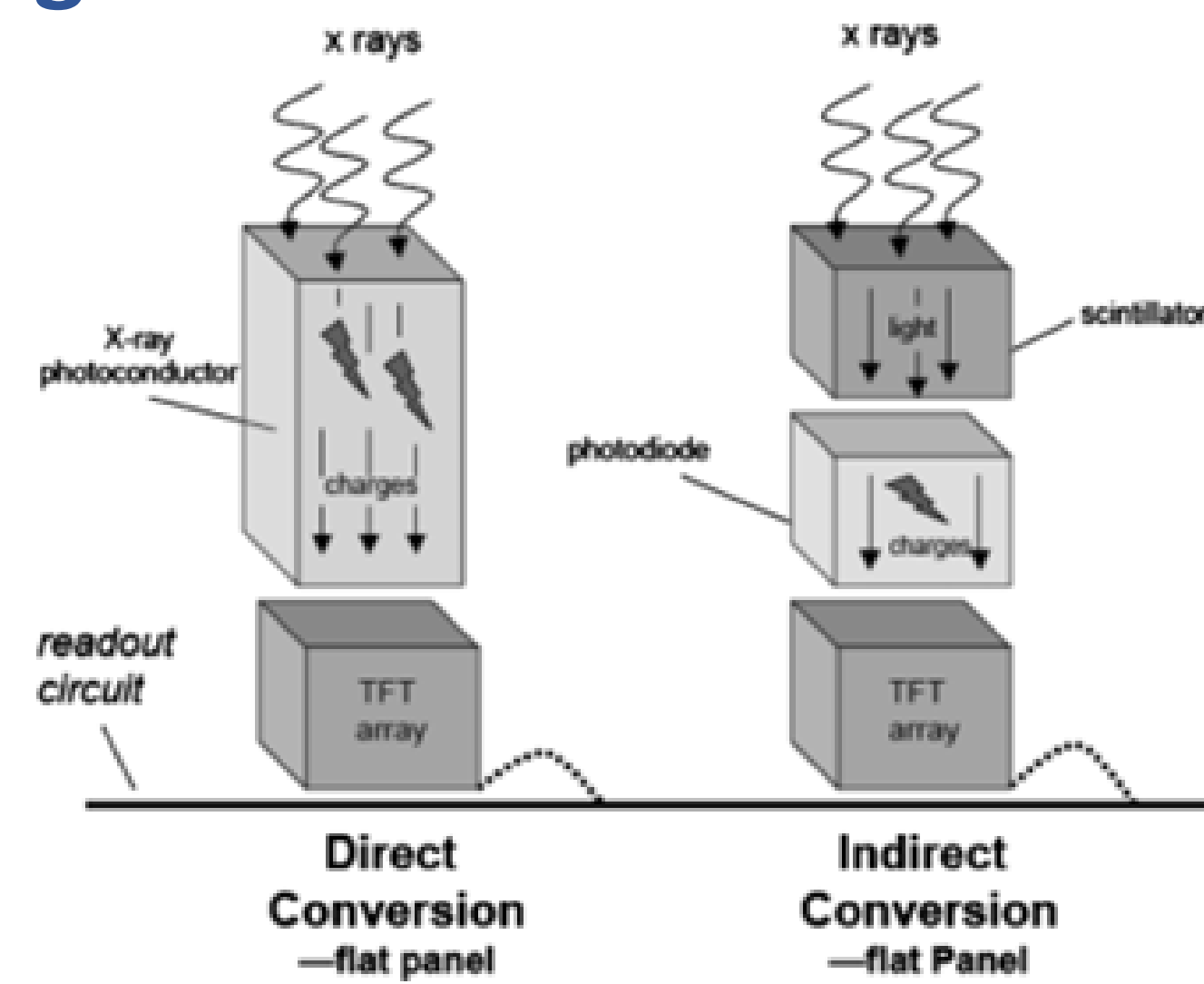


## ALARA imaging

Radiation medical imaging is the cornerstone of diagnostic medicine. In Canada, CT was the most used diagnostic imaging modality in 2019-2020 [1]. However, the radiation utilized in medical imaging is **ionizing radiation** which has drawbacks like **damaging effects on DNA that can lead to cancers**. To reduce this risk a new protocol has emerged of **using a dose that is As Low As Reasonably Achievable (ALARA)** during imaging.



## Digital Solid State Flat Panel Radiation Detectors

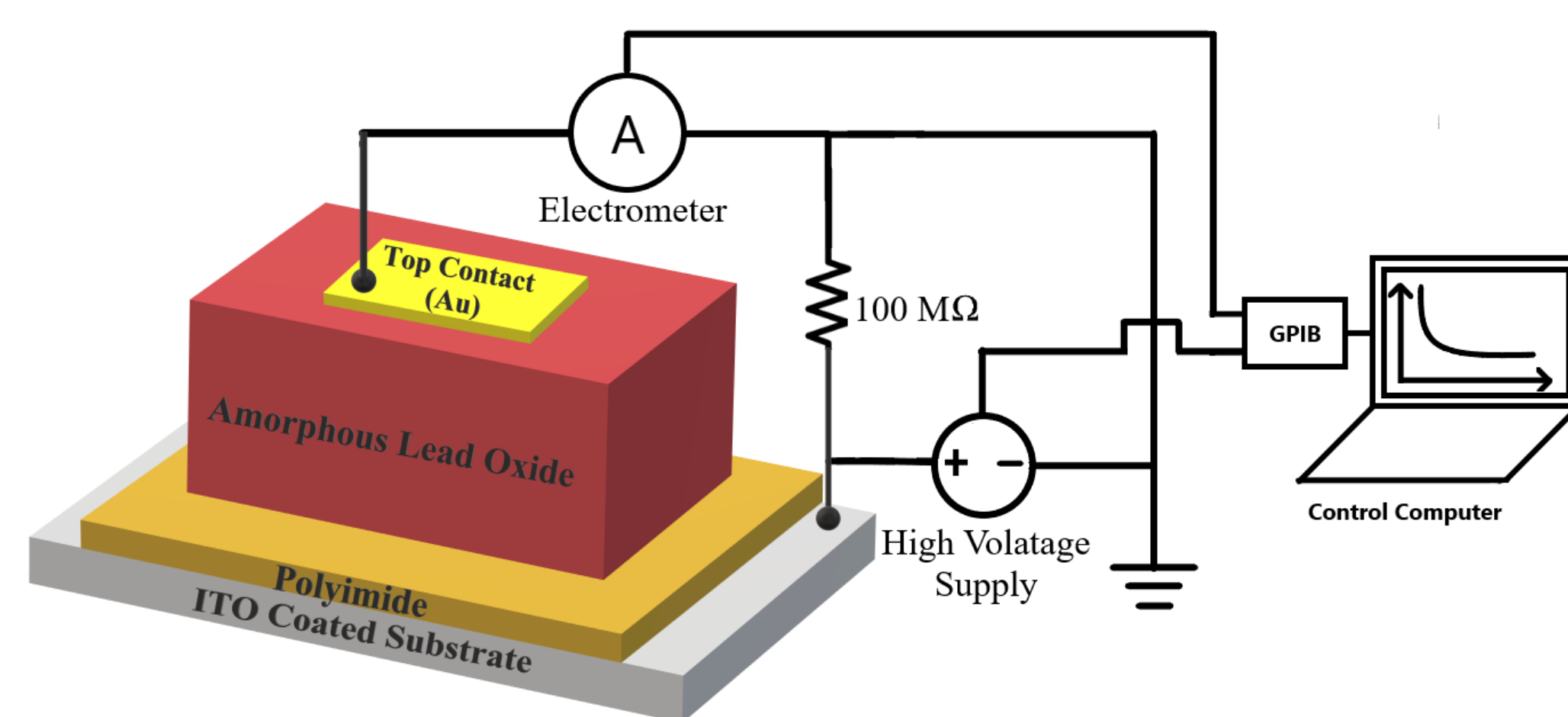


New direct conversion radiation detectors are making ALARA adherence possible. **Direct conversion** boasts better image contrast due to **high spatial resolution and excellent signal-to-noise (SNR) ratios** compared to their indirect counterpart [3]. Currently, the only commercially used direct conversion detector is based on a layer of **amorphous selenium (a-Se)** that revolutionized mammography with **unmatched performance and sensitivity**. However, a-Se low atomic number ( $Z=34$ ) makes it **impractical for use in higher energy diagnostic imaging**. The search for an ideal photoconductive material for high-energy direct conversion detectors is underway.

❖ **Figure 1.** Schematic diagram illustrating the different x-ray-to-charge conversion methods in detectors [2].

## Experimental Setup: Dark Current Kinetics

Dark current was measured as a function of time for a **variety of a-PbO, blocking layer thicknesses, and applied voltages**. Fields practical for detector operation range from **5 – 20V/μm** and such were utilized during experiments. A Stanford Research Systems PS350 power supply applied a **positive bias to the ITO contact** and the **dark current was recorded** by a Keithley 35617EBS electrometer. To avoid any photogenerated carriers during the bias and drain any previously trapped charge, the sample was installed within a light-tight box and allowed to rest in a short-circuit fashion for at least 1 hour.



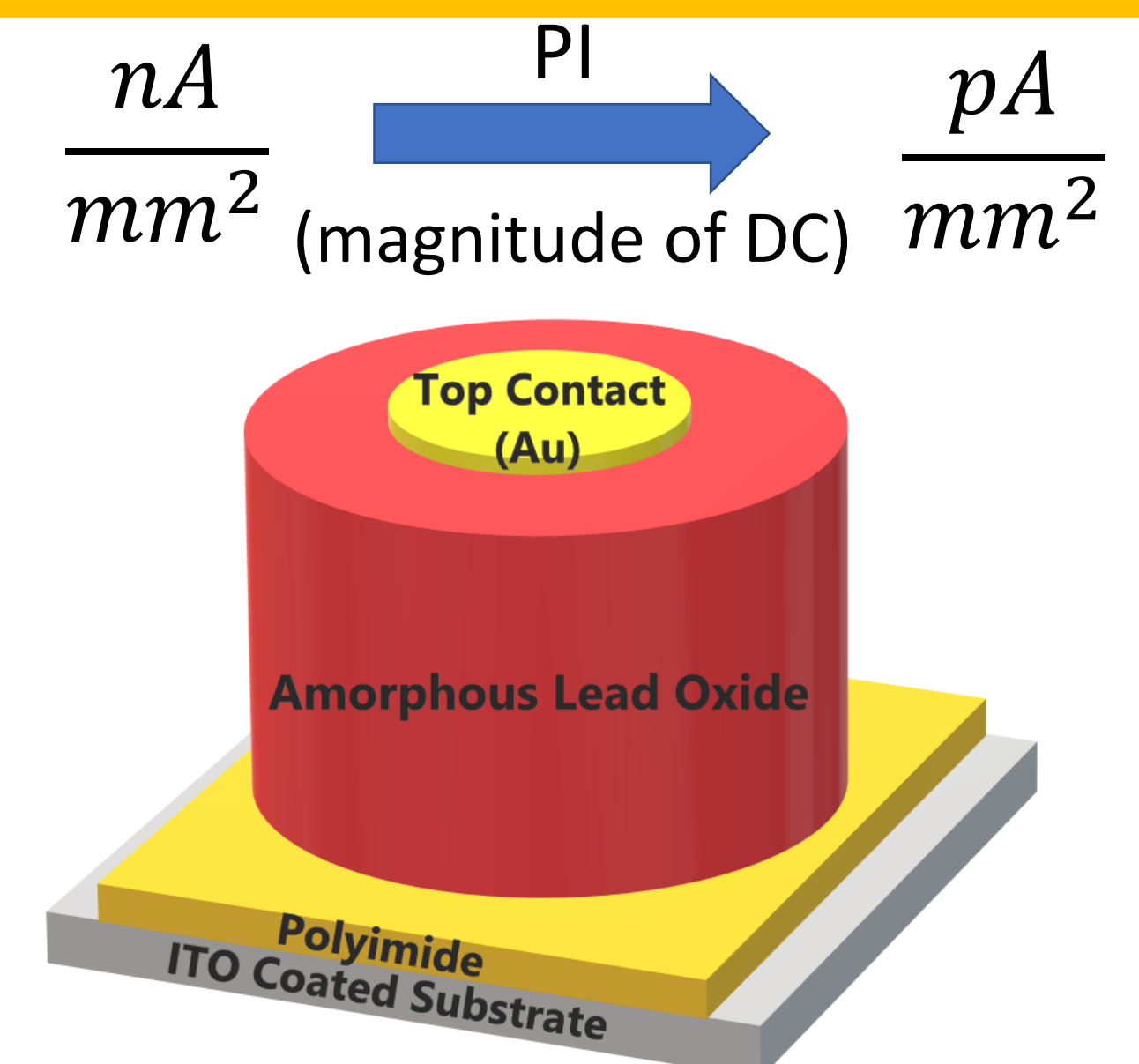
❖ **Figure 3.** Schematic diagram of PI/a-PbO sample structure as well as experimental setup for DC kinetics measurements.

Material	Criteria for the Ideal Photoconductor		
	Sensitivity	Low Intrinsic Noise	Temporal Performance
$\text{BiI}_3$	✓	✓	✗
$\text{PbI}_2$	✓	✗	✗
$\text{HgI}_2$	✓	✓	✗
$\text{ZnO}$	✗	✓	✗
$\text{CdTe}$	✓	✓	✗
$\text{Cd}_{1-x}\text{Zn}_x\text{Te}$	✓	✓	✗
Perovskites	✓	✓	✗
<b>Amorphous Lead Oxide (a-PbO)</b>	✓	✓	✓

❖ **Table 1.** Materials currently under investigation for use in high energy direct conversion detectors.

## Methodology: Optimization of Structure and Operational Parameters

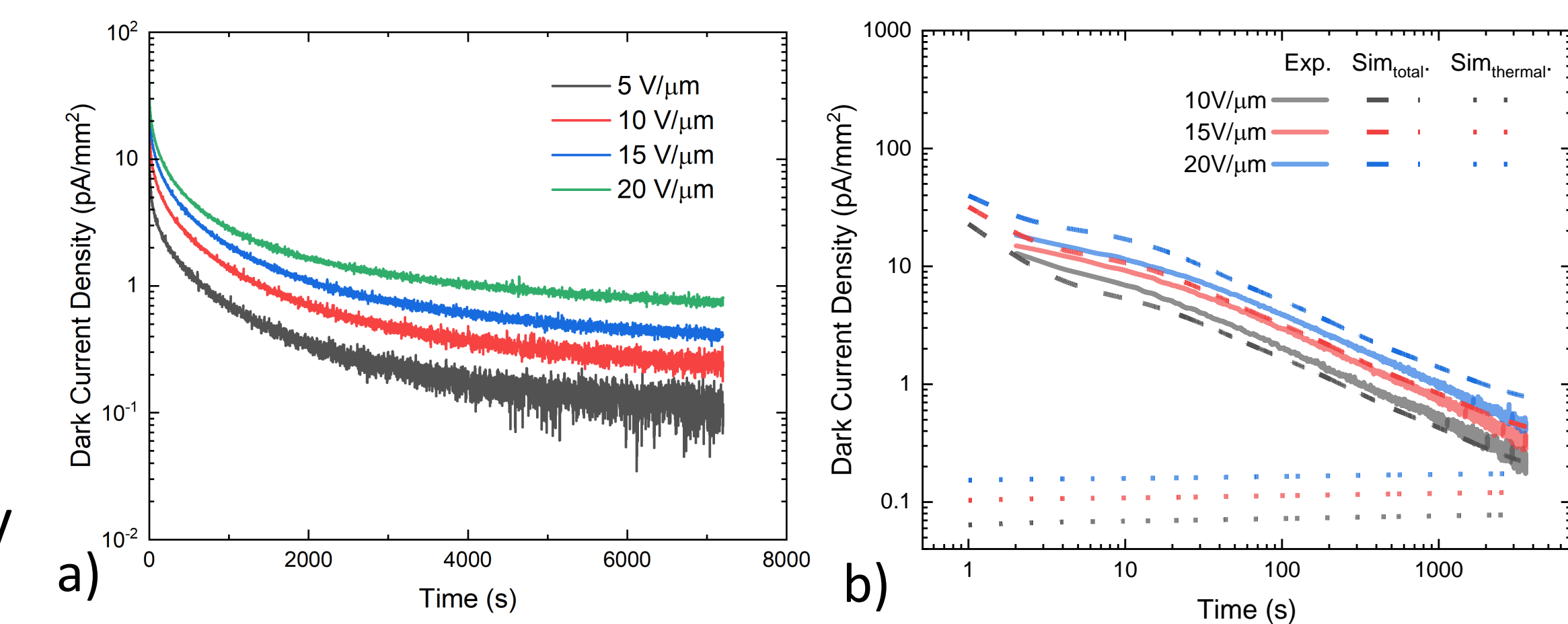
The **flow of current** through a biased photoconductor, in the absence of any irradiation (**dark current (DC)**), constitutes **intrinsic noise** of the material. **SNR** and by extension **image contrast** are **degraded by an increase in DC**. Thus, in practice, **DC** should be kept at a minimum of **1pA/mm<sup>2</sup>** [5]. Previous experiments have shown that a layer of **polyimide (PI)** sandwiched between the biased electrode and a-PbO x-ray photoconductor layers, blocks charge injection **reducing DC**. **DC characterization** of PI/a-PbO structures must be performed to find the **optimal PI blocking layer thickness** to receive the ideal SNR. Furthermore, the **mechanisms of DC** must be revealed for precise and practical understanding of preparation/fabrication property relationship in a-PbO detectors. These factors are essential to achieve desired detector performance.



❖ **Figure 2.** Schematic representation of the structure of a PI/a-PbO sample.

## Results: Dark Current Kinetics and Modeling

- ❖ At all fields **DC decayed** exponentially with time, by nearly **2 orders of magnitude, saturating below 1pA/mm<sup>2</sup>** after 2 hours.
- ❖ A **mathematical model** to account for the decay of DC was derived.
- ❖ The model considers the **injection of charge carriers into the PI layer through** the metal contact as the main source of DC. **Thermal generation** of charge within the bulk of a-PbO layer **contributes negligibly to DC** [6].
- ❖ The **electric field redistribution** within the structure was evaluated by **solving Poisson's equation** with the condition that the total voltage drop over the sample is equal to the applied bias.
- ❖ As time progresses, post bias application, charge is **accumulated at the PI – a-PbO interface**, effectively screening the applied electric field and decreasing injection, hence decreasing DC.
- ❖ **1 – 1.1μm of PI** is shown to be a practical approach to **suppress injection** of charge from the metal contact and **reduce DC** in detectors to acceptable levels **below 1pA/mm<sup>2</sup>** at all fields practical for detector operation.



❖ **Figure 4.** a) Experimentally measured DC as a function of time, of a sample consisting of 1.1μm PI + 18.5μm a-PbO, at various applied fields. b) Experimentally measured DC (solid lines), simulated DC (dashed lines) and simulated thermal component (dotted lines) of DC as a function of time, of a sample consisting of 1μm PI + 10μm a-PbO, at various applied fields.

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## Acknowledgments

- ❖ Lakehead University Physics Departments
- ❖ Dr. Alla Reznik
- ❖ Sasha Grynko
- ❖ A special thanks to all of Dr. Reznik's research team for support and guidance in this project.
- ❖ Teledyne DALSA